2N3766 2N3767

SILICON NPN POWER TRANSISTORS



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3766 and 2N3767 are silicon NPN power transistors manufactured by the epitaxial base process designed for power amplifier and medium speed switching applications.





MAXIMUM F Collector-Ba	RATINGS: (T _C =25°C) se Voltage	SYMBOL V _{CBO}	2N3766 80	2N3767 100	UNITS V
Collector-Em	nitter Voltage	V_{CEO}	60	80	V
Emitter-Base Voltage		V_{EBO}	6.0		V
Continuous Collector Current		$I_{\mathbb{C}}$	4.0		Α
Continuous Base Current		I_{B}	2.0		Α
Power Dissipation		P_{D}	25		W
Operating and Storage Junction Temperature		T _J , T _{stg}	-65 to +200		°C
Thermal Resistance		ΘJC	7.0		°C/W
ELECTRICA	L CHARACTERISTICS: (T _C =25°C ι	unless otherwise	noted)		
SYMBOL	TEST CONDITIONS	MIN	M	ΑX	UNITS
I _{CBO}	V _{CB} =Rated V _{CBO}		1	0	μΑ
I _{CEV}	V_{CE} =Rated V_{CEO} , V_{EB} =1.5 V		1	0	μΑ
ICEO	V _{CF} =Rated V _{CFO}		50	00	μA

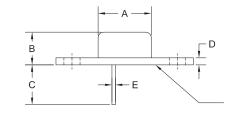
			UNITS
V _{CB} =Rated V _{CBO}	191114	10	μΑ
V _{CE} =Rated V _{CEO} , V _{EB} =1.5V		10	μΑ
V _{CE} =Rated V _{CEO}		500	μΑ
V _{EB} =6.0V		500	μΑ
I _C =100mA (2N3766)	60		V
I _C =100mA (2N3767)	80		V
I _C =500mA, I _B =50mA		1.0	V
I _C =1.0A, I _B =100mA		2.5	V
V_{CE} 10V, I_{C} =1.0A		1.5	V
V_{CE} =5.0V, I_{C} =50mA	30		
V_{CE} =5.0V, I_{C} =500mA	40	160	
V_{CE} =10V, I_{C} =1.0A	20		
V_{CE} =10V, I_{C} =500mA, f=10MHz	10		MHz
V_{CB} =10V, I_E =0, f=100kHz		50	pF
	TEST CONDITIONS V _{CB} =Rated V _{CBO} V _{CE} =Rated V _{CEO} , V _{EB} =1.5V V _{CE} =Rated V _{CEO} V _{EB} =6.0V I _C =100mA (2N3766) I _C =100mA (2N3767) I _C =500mA, I _B =50mA I _C =1.0A, I _B =100mA V _{CE} =1.0A, I _C =500mA V _{CE} =5.0V, I _C =500mA V _{CE} =10V, I _C =1.0A V _{CE} =10V, I _C =500mA, f=10MHz	TEST CONDITIONS V _{CB} =Rated V _{CBO} V _{CE} =Rated V _{CEO} , V _{EB} =1.5V V _{CE} =Rated V _{CEO} V _{EB} =6.0V I _C =100mA (2N3766) 60 I _C =100mA (2N3767) 80 I _C =500mA, I _B =50mA I _C =1.0A, I _B =100mA V _{CE} 10V, I _C =1.0A V _{CE} =5.0V, I _C =50mA 30 V _{CE} =5.0V, I _C =500mA 40 V _{CE} =10V, I _C =1.0A 20 V _{CE} =10V, I _C =500mA, f=10MHz 10	VCB=Rated VCBO 10 VCE=Rated VCEO, VEB=1.5V 10 VCE=Rated VCEO 500 VEB=6.0V 500 IC=100mA (2N3766) 60 IC=100mA (2N3767) 80 IC=500mA, IB=50mA 1.0 IC=1.0A, IB=100mA 2.5 VCE10V, IC=1.0A 1.5 VCE=5.0V, IC=50mA 30 VCE=5.0V, IC=500mA 40 160 VCE=10V, IC=1.0A 20 VCE=10V, IC=500mA, f=10MHz 10

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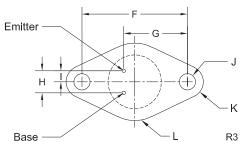
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TO-66 CASE - MECHANICAL OUTLINE



Seating Plane: The seating plane must be within 0.001" concave to 0.004" convex within 0.600" diameter from the center of the device.



MARKING: FULL PART NUMBER

DIMENSIONS								
	INCHES		MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
A (DIA)	0.470	0.500	11.94	12.70				
В	0.250	0.340	6.35	8.64				
С	0.360	-	9.14	-				
D	0.050	0.075	1.27	1.91				
E (DIA)	0.028	0.034	0.71	0.86				
F	0.956	0.964	24.28	24.48				
G	0.570	0.590	14.48	14.99				
Н	0.190	0.210	4.83	5.33				
I	0.093	0.107	2.36	2.72				
J (DIA)	0.142	0.152	3.61	3.86				
K (RAD)	0.141		3.58					
L (RAD)	0.345		8.76					

TO-66 (REV:R3)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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